



CORRECTION

Correction to: Solution-Processed Insulators for Flexible Metal-Insulator-Metal Structures

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In the original article, there is an error in the legend in Fig. 4. Following is the corrected figure:

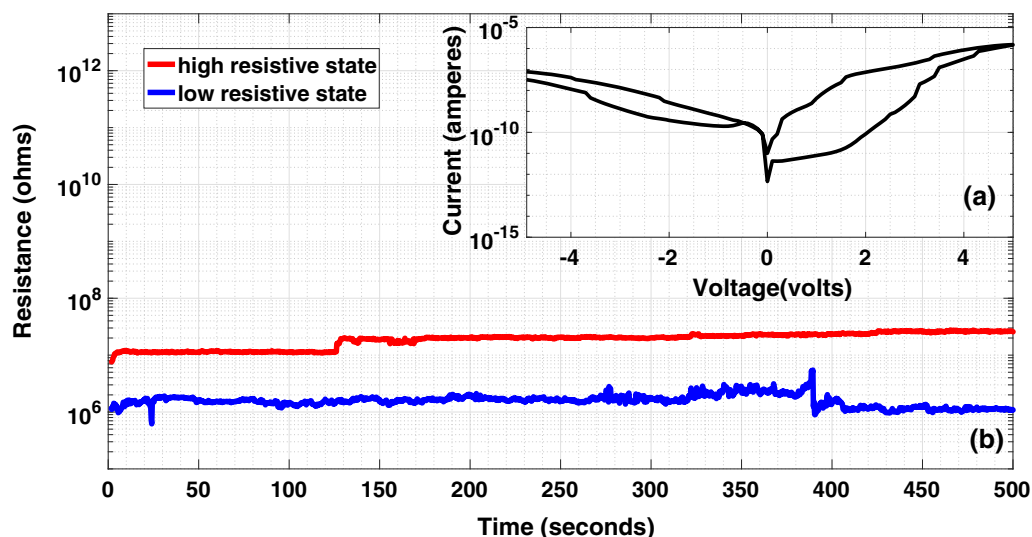


Fig. 4. Electrical characterization: (a) current–voltage characteristics of the device with Au and Ag contacts, (b) retention characteristics.

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